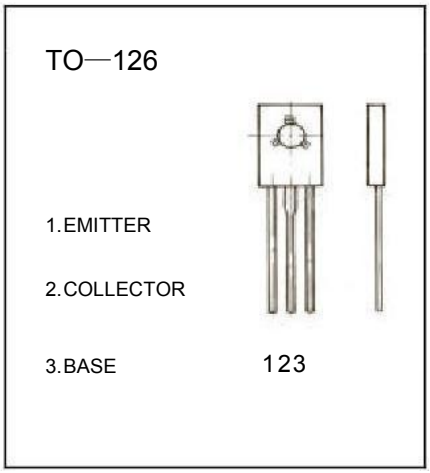
TO-126 Plastic-Encapsulate Transistors

D1691 TRANSISTOR（ NPN ）



FEATURES

Power dissipation

P_{CM}: 1.3 W（Tamb=25℃）

Collector current

I_{CM}: 8.0 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector cut-off current	I_{CBO}	V_{CB}=50V, I_E=0			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=7.0V, I_C=0			10	μA
DC currentgain	$h_{FE(1)}$	V_{CE}=1V, I_C=0.1A		60		
DC currentgain	$h_{FE(2)}$	V_{CE}=1V, I_C=2.0A		100	400	
DC currentgain	$h_{FE(3)}$	V_{CE}=1V, I_C=5.0A		50		
Collector-saturation voltage	$V_{CE(sat)}$	I_C=2A, I_B=0.2A		0.1	0.3	V
Base-saturation voltage	V_{BE}	I_C=2A, I_B=0.2A		0.9	1.2	V

CLASSIFICATION OF $h_{FE(1)}$

Rank	M	L	K
Range	100-200	160-320	200-400